ABSTRACT

There is provided an underlayer coating causing no intermixing with photoresist layer and having a high dry etching rate compared with photoresist, which is used in lithography process of manufacture of semiconductor device. Concretely, it is an underlayer coating forming composition for forming a porous underlayer coating for use in manufacture of semiconductor device, comprising a blowing agent, an organic material and a solvent, or a polymer having a blowing group and a solvent. The underlayer coating formed from the composition has porous structure which has pores therein, and makes possible to attain a high dry etching rate.